

2SK711

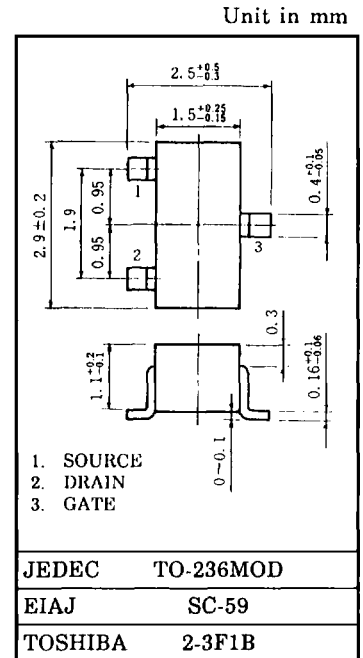
SILICON N CHANNEL JUNCTION TYPE FIELD EFFECT TRANSISTOR

HIGH FREQUENCY AMPLIFIER APPLICATIONS.
AM HIGH FREQUENCY AMPLIFIER APPLICATIONS.
AUDIO FREQUENCY AMPLIFIER APPLICATIONS.

- High $|Y_{fs}|$: $|Y_{fs}|=25\text{mS}$ (Typ.)
- Low C_{iss} : $C_{iss}=7.5\text{pF}$ (Typ.)

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Gate-Drain Voltage	V_{GDS}	-20	V
Gate Current	I_G	10	mA
Drain Power Dissipation	P_D	150	mW
Junction Temperature	T_j	125	°C
Storage Temperature Range	T_{stg}	-55~125	°C



Weight : 0.012g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Gate Leakage Current	I_{GSS}	$V_{GS} = -15\text{V}, V_{DS} = 0\text{V}$	—	—	-1.0	nA
Gate-Drain Breakdown Voltage	$V_{(BR)GDS}$	$V_{DS} = 0\text{V}, I_G = -100\mu\text{A}$	-20	—	—	V
Drain Current	I_{DSS} (Note)	$V_{DS} = 5\text{V}, V_{GS} = 0\text{V}$	6	—	32	mA
Gate-Source Cut-off Voltage	$V_{GS(OFF)}$	$V_{DS} = 5\text{V}, I_D = 1\mu\text{A}$	—	—	-2.5	V
Forward Transfer Admittance	$ Y_{fs} $	$V_{DS} = 5\text{V}, V_{GS} = 0\text{V}, f = 1\text{kHz}$	15	25	—	mS
Input Capacitance	C_{iss}	$V_{DS} = 5\text{V}, V_{GS} = 0\text{V}, f = 1\text{MHz}$	—	7.5	10	pF
Reverse Transfer Capacitance	C_{rss}	$V_{DS} = 5\text{V}, I_D = 0\text{mA}, f = 1\text{MHz}$	—	2	3	pF

Note: I_{DSS} Classification

GR: 6~12mA, BL: 10~20mA, V: 16~32mA
(G) (L) (V)

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Marking

